Abstract

Etching method and devices produced using the etching method

A double ITO structure, containing sequential layers of ITO (Indium tin oxide), Silicon Dioxide (which may include a dopant material) and ITO, is selectively protected by a patterned photo-resist mask. The sequential layers are etched together in a single etching step using an etchant composition which is an acidic solution containing a transition metal chloride and Hydrochloric acid (HCl). Thus, the double ITO structure is etched using a substantially fluoride-free etchant composition.

[Figure to accompany the abstract: FIG. 2]

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